

## Description

The GBL03C-A is a 3.3V bi-directional TVS diode, utilizing leading monolithic silicon technology to provide fast response time and low ESD clamping voltage, making this device an ideal solution for protecting voltage sensitive high-speed data lines. The GBL03C-A has a low capacitance with a typical value at 1pF, and complies with the IEC 61000-4-2 (ESD) with  $\pm 30\text{kV}$  air and  $\pm 30\text{kV}$  contact discharge. It is assembled into a lead-free SOD-323 package. The small size, low capacitance and high ESD surge protection make GBL30C-A an ideal choice to protect cell phone, wireless systems, and communication equipment.

## Features

- 340W peak pulse power (8/20 $\mu\text{s}$ )
- Ultra low capacitance: 1pF typical
- Ultra low leakage: nA level
- Operating voltage: 3.3V
- Low clamping voltage
- Protects one power line or data line
- Complies with following standards:
  - IEC 61000-4-2 (ESD) immunity test  
Air discharge:  $\pm 30\text{kV}$   
Contact discharge:  $\pm 30\text{kV}$
  - IEC61000-4-5 (Lightning) 21A (8/20 $\mu\text{s}$ )
- RoHS Compliant

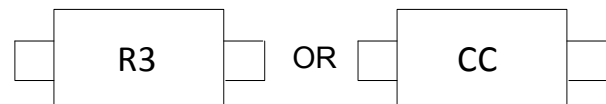
## Mechanical Characteristics

- Package: SOD-323
- Lead Finish: Matte Tin
- Case Material: “Green” Molding Compound.
- Moisture Sensitivity: Level 3 per J-STD-020
- Terminal Connections: See Diagram Below
- Marking Information: See Below

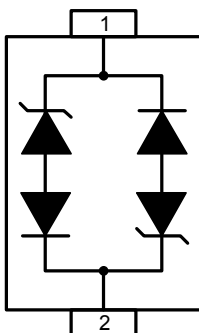
## Applications

- USB Ports
- Smart Phones
- Wireless Systems
- Ethernet 10/100/1000 Base T

## Marking Information



## Dimensions and Pin Configuration



Circuit and Pin Schematic

## Ordering Information

Part Number	Packaging	Reel Size
GBL03C-A	3000/Tape & Reel	7 inch

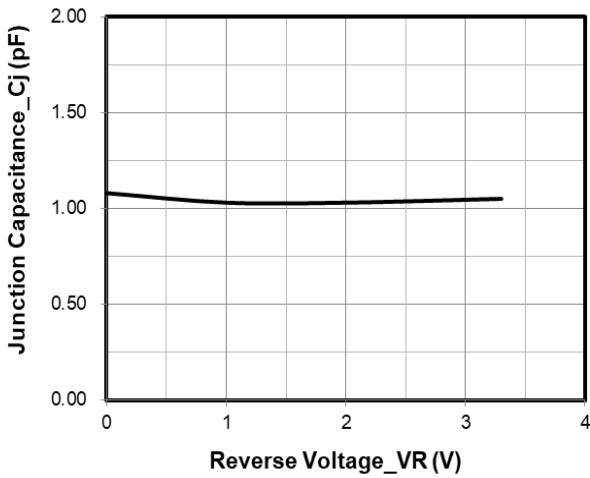
**Absolute Maximum Ratings ( $T_A=25^{\circ}\text{C}$  unless otherwise specified)**

Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20 $\mu\text{s}$ )	Ppk	340	W
Peak Pulse Current (8/20 $\mu\text{s}$ )	I <sub>PP</sub>	21	A
ESD per IEC 61000-4-2 (Air)	V <sub>ESD</sub>	$\pm 30$	kV
ESD per IEC 61000-4-2 (Contact)		$\pm 30$	
Operating Temperature Range	T <sub>J</sub>	-55 to +125	$^{\circ}\text{C}$
Storage Temperature Range	T <sub>stg</sub>	-55 to +150	$^{\circ}\text{C}$

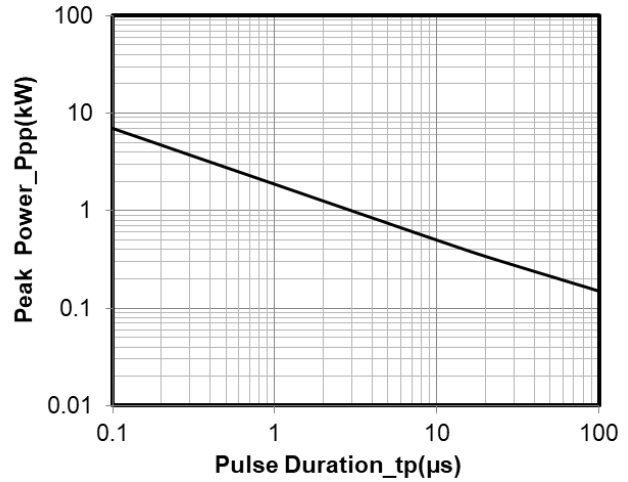
**Electrical Characteristics ( $T_A=25^{\circ}\text{C}$  unless otherwise specified)**

Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Working Voltage	V <sub>RWM</sub>			3.3	V	
Punch-Through Voltage	V <sub>PT</sub>	3.5			V	I <sub>T</sub> = 2 $\mu\text{A}$
Snap-Back Voltage	V <sub>BR</sub>	2.8			V	I <sub>T</sub> = 50mA
Reverse Leakage Current	I <sub>R</sub>			0.2	$\mu\text{A}$	V <sub>RWM</sub> = 3.3V
Clamping Voltage	V <sub>C</sub>			5	V	I <sub>PP</sub> = 1A (8 x 20 $\mu\text{s}$ pulse)
Clamping Voltage	V <sub>C</sub>			16	V	I <sub>PP</sub> = 21A (8 x 20 $\mu\text{s}$ pulse)
Junction Capacitance	C <sub>J</sub>		1		pF	V <sub>R</sub> = 0V, f = 1MHz

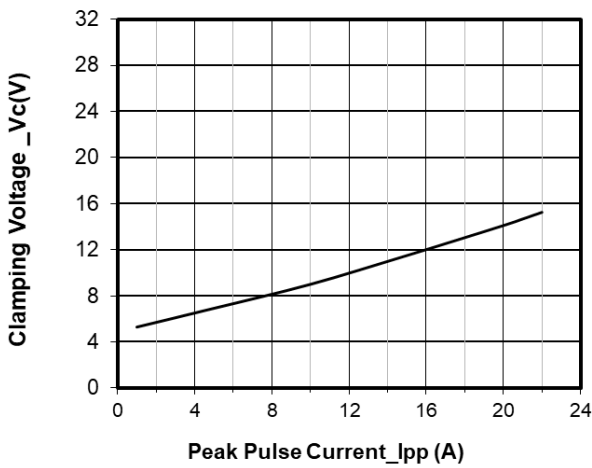
**Typical Performance Characteristics (TA=25°C unless otherwise Specified)**



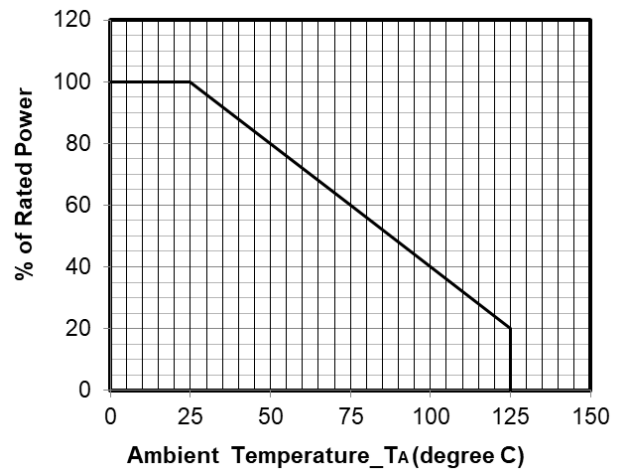
**Junction Capacitance vs. Reverse Voltage**



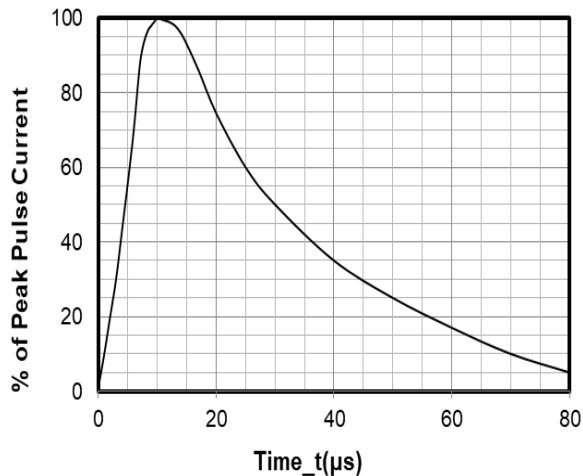
**Peak Pulse Power vs. Pulse Time**



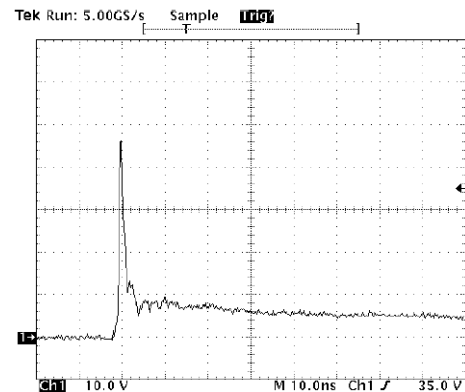
**Clamping Voltage vs. Peak Pulse Current**



**Power Derating Curve**



**8 X 20μs Pulse Waveform**

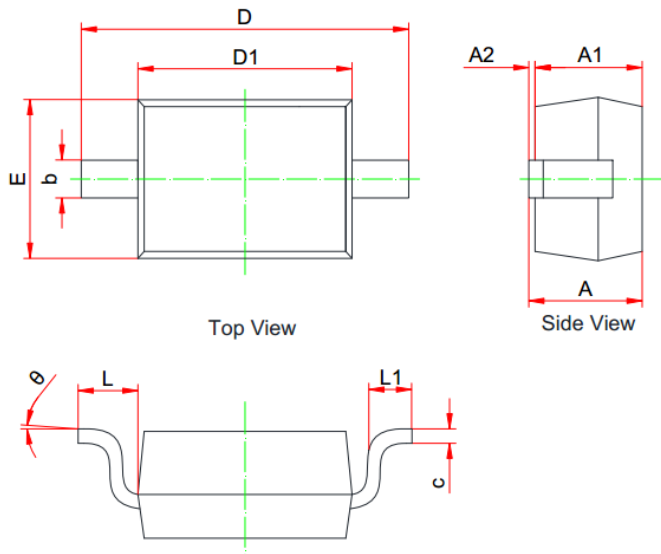


**Note: Data is taken with a 10x attenuator**

**ESD Clamping Voltage**

**8 kV Contact per IEC61000-4-2**

### SOD-323 Package Outline Drawing



SYM	MILLIMETERS		
	MIN	NOM	MAX
A	0.800	--	1.100
A1	0.800	--	0.900
A2	0.000	--	0.100
b	0.250	--	0.400
c	0.080	--	0.177
D1	1.600	1.700	1.800
D	2.300	--	2.800
E	1.150	--	1.400
L	0.475REF		
L1	0.100	--	0.500
Θ	0°	--	8°

### Suggested Land Pattern



**Unit: mm**

### Contact Information

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